



DMMT5551/DMMT5551S

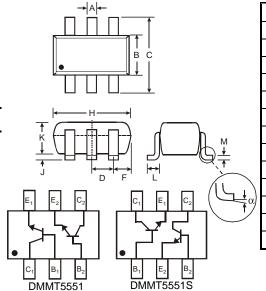
MATCHED NPN SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features

- **Epitaxial Planar Die Construction**
- Complementary PNP Type Available (DMMT5401)
- Ideal for Low Power Amplification and Switching
- Intrinsically Matched NPN Pair (Note 1)
- 2% Matched Tolerance, hFE, VCE(SAT), VBE(SAT)
- Lead Free/RoHS Compliant (Note 4)
- "Green" Device (Note 5 and 6)

Mechanical Data

- Case: SOT-26
- Case Material: Molded Plastic, "Green" Molding Compound, Note 7. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Copper leadframe).
- Marking Information: K4R & K4T, See Page 3
- Ordering & Date Code Information: See Page 3
- Weight: 0.006 grams (approximate)



SOT-26									
Dim	Min	Max	Тур						
Α	0.35	0.50	0.38						
В	1.50	1.70	1.60						
C	2.70	3.00	2.80						
D	_	_	0.95						
F			0.55						
H	2.90	3.10	3.00						
7	0.013	0.10	0.05						
K	1.00	1.30	1.10						
L	0.35	0.55	0.40						
М	0.10	0.20	0.15						
α	0°	8°	_						
All Dimensions in mm									

Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	180	V
Collector-Emitter Voltage	V _{CEO}	160	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current - Continuous (Note 2)	I _C	200	mA
Power Dissipation (Note 2, 3)	P _d	300	mW
Thermal Resistance, Junction to Ambient (Note 2)	$R_{ hetaJA}$	417	°C/W
Operating and Storage Temperature Range	T _j , T _{STG}	-55 to +150	°C

DMMT5551

(K4R Marking Code) (K4T Marking Code)

Notes:

- Built with adjacent die from a single wafer.
- Device mounted on FR5 PCB: 1.0 x 0.75 x 0.62 in.; pad layout as shown on suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- 3. Maximum combined dissipation.
- No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

 Product manufactured with Date Code 0627 (week 27, 2006) and newer are built with Green Molding Compound. Product manufactured prior to Date Code 0627 are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

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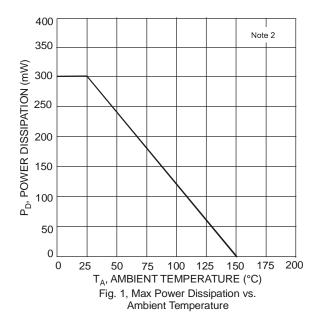


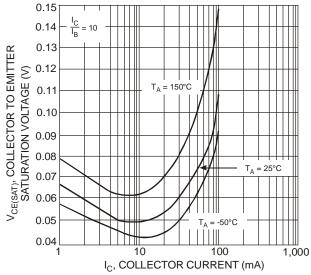
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition				
OFF CHARACTERISTICS (Note 7)									
Collector-Base Breakdown Voltage	V _{(BR)CBO}	180		V	$I_C = 100 \mu A, I_E = 0$				
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	160		V	$I_C = 1.0 \text{mA}, I_B = 0$				
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	6.0		V	$I_E = 10\mu A, I_C = 0$				
Collector Cutoff Current	I _{CBO}		50	nA	V _{CB} = 120V, I _E = 0				
Concessor Caton Carrent	ICBO			μΑ	$V_{CB} = 120V, I_E = 0, T_A = 100^{\circ}C$				
Emitter Cutoff Current	I _{EBO}	_	50	nA	$V_{EB} = 4.0V, I_C = 0$				
ON CHARACTERISTICS (Note 7)									
		80	_		$I_C = 1.0 \text{mA}, V_{CE} = 5.0 \text{V}$				
DC Current Gain (Note 8)	h _{FE}	80	250	_	$I_C = 10 \text{mA}, V_{CE} = 5.0 \text{V}$				
		30			$I_C = 50 \text{mA}, V_{CE} = 5.0 \text{V}$				
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	0.15 0.20	V	$I_C = 10mA, I_B = 1.0mA$				
Collector-Emitter Saturation Voltage					$I_C = 50 \text{mA}, I_B = 5.0 \text{mA}$				
Base-Emitter Saturation Voltage	V		1.0	V	$I_C = 10mA$, $I_B = 1.0mA$				
base-Emitter Saturation Voltage	V _{BE(SAT)}		1.0	٧	$I_C = 50 \text{mA}, I_B = 5.0 \text{mA}$				
SMALL SIGNAL CHARACTERISTICS									
Output Capacitance	C _{obo}	_	6.0	pF	$V_{CB} = 10V$, $f = 1.0MHz$, $I_E = 0$				
Small Signal Current Gain	h _{FE}	50	250		$V_{CE} = 10V, I_{C} = 1.0mA,$				
Official Signal Surfer Surf	''FE		200		f = 1.0kHz				
Current Gain-Bandwidth Product	f⊤	100	300	MHz	$V_{CE} = 10V, I_{C} = 10mA,$ f = 100MHz				
Noice Figure	NF	•	8.0	dB	$V_{CE} = 5.0V$, $I_C = 200\mu A$,				
Noise Figure	INF		6.0	ūĎ	$R_S = 1.0k\Omega$, $f = 1.0kHz$				

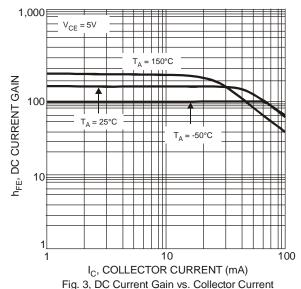
Notes:

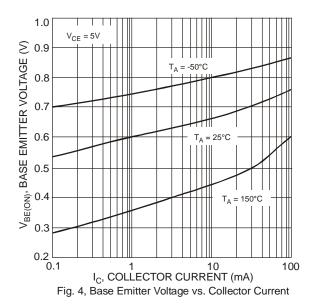
- Short duration pulse test used to minimize self-heating effect. The DC Current Gain, h_{FE} , (matched at I_C = 10mA and V_{CE} = 5V) Collector Emitter Saturation Voltage, $V_{CE(SAT)}$, and Base Emitter Saturation Voltage, $V_{BE(SAT)}$ are matched with typical matched tolerances of 1% and maximum of 2%.











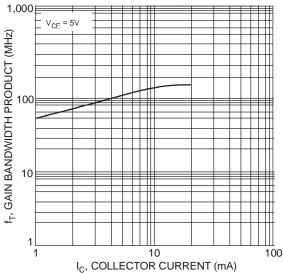


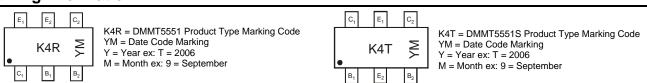
Fig. 5, Gain Bandwidth Product vs. Collector Current

Ordering Information (Note 6 & 9)

Device	Packaging	Shipping
DMMT5551-7-F	SOT-26	3000/Tape & Reel
DMMT5551S-7-F	SOT-26	3000/Tape & Reel

Notes: 9. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



Date Code Key										
Year	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	Р	R	S	Т	U	V	W	Х	Υ	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



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